

Product Summary

BV _{DSS}	Rds(on) max	I _D max T _A = +25°C
	$25m\Omega @ V_{GS} = 4.5V$	6.0A
20V	31mΩ @ V _{GS} = 2.5V	5.1A

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- **Battery Management Application**
- **Power Management Functions**
- **DC-DC** Converters

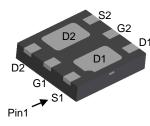
Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4)
- Weight: 0.0065 grams (Approximate)





U-DFN2020-6 (Type B)

Bottom View

D1 G1 G1 Protection Gate Protection **S1** Diode Diode **Q1 N-CHANNEL MOSFET Q2 N-CHANNEL MOSFET**

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2025UFDB-7	U-DFN2020-6 (Type B)	3000/Tape & Reel
DMN2025UFDB-13	U-DFN2020-6 (Type B)	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

D1

S1



Marking Information

Site 1



O5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	E		Н		J	К	L	М	Ν	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



O5 = Product Type Marking Code YWX = Date Code Marking

Y = Year (ex: 0 = 2020)

W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	7		0	1	2	3	4	5	6	7	8	9
Week		1-	-26 27-52				53					
Code		A	-Z			а	-Z			2	2	
Internal Code	Sur	n 🗌	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	V	Х		Y		Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	V _{GSS}	±10	V		
Continuous Drain Current (Note 6) V _{GS} = 4.5V	ID	6.0 4.8	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	<i>б</i>)		Ідм	35	A
Continuous Source-Drain Diode Current			ls	2	А
Avalanche Current (Note 7) L = 0.1mH	las	12	A		
Avalanche Energy (Note 7) L = 0.1mH			Eas	8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	170	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	98	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	22	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Cymbel		. 76	max	Unit	
Drain-Source Breakdown Voltage	BVDSS	20	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	—		1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	lgss	—		±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						·
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	Deserve		18.5	25	mΩ	V _{GS} = 4.5V, I _D = 4A
Static Drain-Source On-Resistance	RDS(ON)	_	26	31	11152	V _{GS} = 2.5V, I _D = 4A
Diode Forward Voltage	Vsd	—	0.7	1.2	V	Vgs = 0V, Is = 5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	—	486	—		
Output Capacitance	Coss	—	92	—	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	—	77	—		1 - 1.00012
Gate Resistance	Rg	—	3.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	5.9	—		
Total Gate Charge (V _{GS} = 10V)	Qg	—	12.3	—	nC	
Gate-Source Charge	Qgs	—	0.8	—	nc	$V_{DS} = 10V, I_{D} = 6.5A$
Gate-Drain Charge	Q _{gd}	—	2.2	—		
Turn-On Delay Time	t _{D(ON)}	—	3.4	—		
Turn-On Rise Time	tR	—	5.4	—		$V_{DS} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)	—	17.6	—	ns	$R_G = 6\Omega$, $R_L = 10\Omega$, $I_D = 1A$
Turn-Off Fall Time	tF	—	9.3	—	1	
Reverse Recovery Time	t _{RR}	—	7.7	—	ns	I _F = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}		1.5	—	nC	I _F = 1A, di/dt = 100A/µs

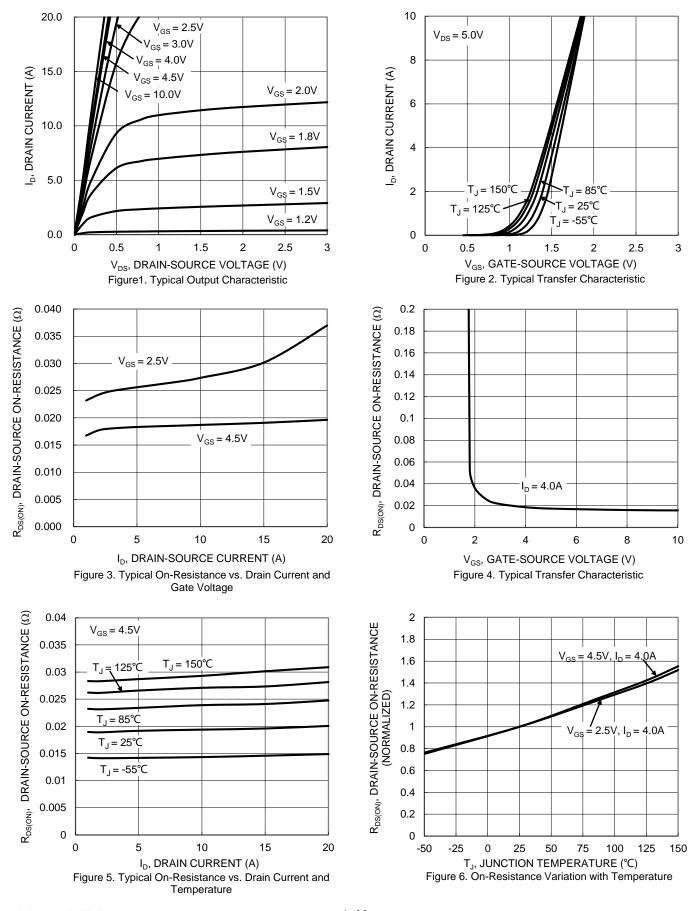
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.



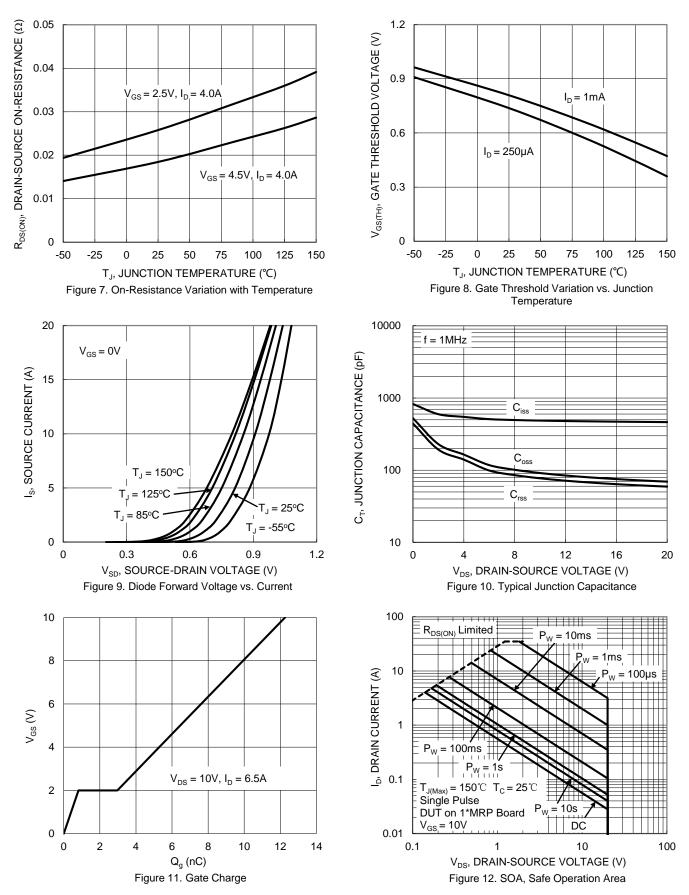
DMN2025UFDB



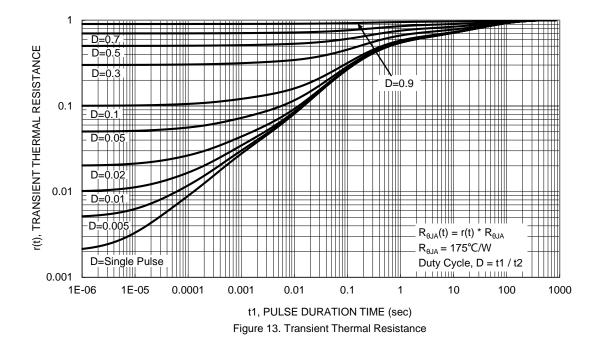
DMN2025UFDB Datasheet number: DS40151 Rev. 4 - 2



DMN2025UFDB



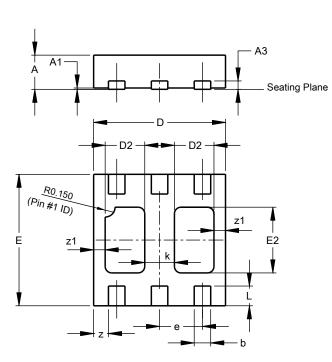






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



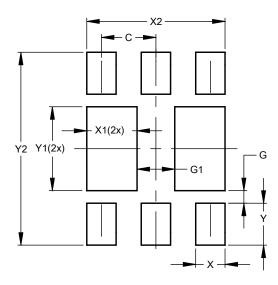
U-DFN2020-6	(Type B)
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	U-DFN Typ	2020-6	
Dim	Min	Max	Тур
Α	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
Е	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All I	Dimens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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